

Docket No.: M4065.0697/P697-A
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
John T. Moore et al.

Application No.: Not Yet Assigned

Confirmation No.:

Filed: February 10, 2004

Art Unit: N/A

For: METHODS OF METAL DOPING
CHALCOGENIDE MATERIAL

Examiner: Not Yet Assigned

INFORMATION DISCLOSURE STATEMENT (IDS)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Pursuant to 37 CFR 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO/SB/08. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement accompanies the new patent application submitted herewith.

Copies of the references on the PTO/SB/08 are not provided.

Those patent(s) or publication(s) which are marked with a double asterisk (**) next to the Cite No. in the attached form PTO/SB/08 (facsimile) are not supplied because they were previously cited by or submitted to the Office in a prior application

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number 09/797,635, filed March 1, 2001 and relied upon in this application for an earlier filing date under 35 U.S.C. 120.

In accordance with 37 CFR 1.97(g), the filing of this Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined in 37 CFR 1.56(a) exists. In accordance with 37 CFR 1.97(h), the filing of this Information Disclosure statement shall not be construed to be an admission that any patent, publication or other information referred to therein is "prior art" for this invention unless specifically designated as such.

It is submitted that the Information Disclosure Statement is in compliance with 37 CFR 1.98 and the Examiner is respectfully requested to consider the listed references.

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0697/P697-A. A duplicate copy of this paper is enclosed.

Dated: February 10, 2004

Respectfully submitted,

By 

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known	
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				First Named Inventor	John T. Moore
				Art Unit	Not Yet Assigned
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U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
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	AB	US 2002/0000666	01/03/2002	Kozicki et al. **	
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	AX	2003/0035315	02/20/03	Kozicki **	

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Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
	BA	WO 97/48032	12/18/1997	Kozicki et al. **		
	BB	WO 99/28914	06/10/1999	Kozicki et al. **		
	BC					
	BD					

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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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Sheet	4	of	8	Attorney Docket Number	M4065.0697-A

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				First Named Inventor	John T. Moore
				Group Art Unit	Not Yet Assigned
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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT John T. Moore et al.			
				FILING DATE March 1, 2001		GROUP 2813	
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AH	5,177,567	01/05/93	Klersy et al. ✕ ✕	257	4		
AI	5,219,788	06/15/93	Abernathey et al. ✕ ✕	437	187		
AJ	5,726,083	03/10/98	Takaishi ✕ ✕	438	210		
AK	5,751,012	05/12/98	Wolstenholme et al. ✕ ✕	257	5		
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	AN	Das et al., <i>Theory of the characteristic curves of the silver chalcogenide glass inorganic photoresists</i> , 54 APPL. PHYS. LETT., No. 18, pp. 1745-1747 (May 1989). ✕ ✕					
	AO	Helbert et al., <i>Intralevel hybrid resist process with submicron capability</i> , SPIE Vol. 333					
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AB	5,841,150	11/24/98	Gonzalez et al. ✕ ✕	257	3		
AC	5,920,788	07/06/99	Reinberg ✕ ✕	438	466		
AD	5,998,066	12/07/99	Block et al. ✕ ✕	430	5		
AE	6,077,729	06/20/00	Harshfield ✕ ✕	438	128		
AF	6,236,059 B1	05/22/01	Wolstenholme et al. ✕ ✕	257	3		
AG	6,297,170 B1	10/02/01	Gabriel et al. ✕ ✕	438	738		
AH	6,300,684 B1	10/09/01	Gonzalez et al. ✕ ✕	257	774		
AI	6,316,784 B1	11/13/01	Zahorik et al. ✕ ✕	257	3		
AJ	6,329,606 B1	12/11/01	Freyman et al. ✕ ✕	174	260		
AK	6,348,365	02/19/02	Moore et al. ✕ ✕	438	130		
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			62 J. AMER. CERAMIC SOC., Nos. 3-4, pp. 183-188 (Mar.-Apr. 1979). ✕ ✕				
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	AD	6,418,049 B1	07/09/02	Kozicki et al. ✕ ✕	365	174	
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	AA	10/077,867	Campbell et al. (as filed) ✕ ✕			02/20/2002	
	AB	10/232,757	Li, et al. ✕ ✕			08/29/2002	
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